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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	Not Yet Assigned
Filing Date	11-09-2001
First Named Inventor	Brian S. Doyle, et al.
Group Art Unit	Not Yet Assigned
Examiner Name	Not Yet Assigned
Attorney Docket Number	42390P5768D

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published
De		G.A. HISHMEH & L. CARTZ, F. DESAGE, C. TEMPLIER, & J.C. DESOYER, R.C. BIRTCHER; Rare Gas Bubbles in Muscovite Mica Implanted with Xenon and Krypton; J. Mater. Res., Vol. 9 No. 12, December 1994, pp. 3095-3107.
		REIJI YAMADA, STEVEN J. ZINKLE, G. PHILIP PELLIS; Microstructure of Al ₂ O ₃ and MgAl ₂ O ₄ Preimplanted with H, He, C and Irradiated with Ar ⁺ ions*; Elsevier Science B.V.; Journal of Nuclear Materials 209 (1994); pp. 191-203.
		E.D. SPECHT, D.A. WALKO, & S.J. ZINKLE; Density Reduction: A Mechanism for Amorphization at High Ion Doses; Mat.Res.Soc.Symp.Proc. Vol. 316; 1994 Materials Research Society, pp. 241-246.
		V. JESCHKE & G.H. FRISCHAT; Gas Bubbles in Glass Melts Under Microgravity. Part 2. Helium Diffusion; Physics and Chemistry of Glasses Vol. 28, No. 5, October 1987; pp. 177-182.
		N. MORIYA, Y. SHACHAM-DIAMOND, R. KALISH; Modification Effects in Ion-Implanted SiO ₂ Spin-on-Glass; J. Electrochem. Soc., Vol. 140, No. 5, May 1993, The Electrochemical Society, Inc., pp. 1442-1450.
		R. SIEGELE, G.C. WEATHERLY & H.K. HAUGEN, D.J. LOCKWOOD, L.M. HOWE; Helium Bubbles in Silicon: Structure and Optical Properties; Appl. Phys. Lett. 66 (11) 13 March 1995, 1995 American Institute of Physics, pp. 1319-1321.
		D. BISERO, F. CORNI, C. NOBILI, R. TONINI, & G. OTTAVIANI, C. MAZZOLENI, L. PAVESI; Visible Photoluminescence from He-implanted Silicon; Appl. Phys. Lett. 67 (23) 4 December 1995; American Institute of Physics; pp. 3447-3449.
		A. VAN VEEN, C.C. GRIFFIOEN, & J.H. EVANS; Helium-Induced Porous Layer Formation in Silicon; Material Research Society, Mat. Res. Soc. Symp. Proc. Vol. 107; pp. 449-454.
		V. RAINERI, G. FALLICA, S. LIBERTINO; Lifetime Control in Silicon Devices by Voids Induced by He Ion Implantation; J. Appl. Phys. 79 (12). 15 June 1996, American Institute of Physics; pp. 9012-9016.
		D.M. FOLLSTAEDT, S.M. MYERS, S.R. LEE, J.L. RENO, R.L. DAWSON & J. HAN; Interaction of Cavities and Dislocations in Semiconductors; Mat. Res. Soc. Symp. Proc. Vol. 438, 1997 Materials Research Society, pp. 229-234.
De		J.W. MEDERNACH, T.A. HILL, S.M. MYERS, AND T.J. HEADLEY; Microstructural Properties of Helium Implanted Void Layers in Silicon as Related to Front-Side Gettering; J. Electrochem. Vol. 143, No. 2, February 1996, The Electrochemical Society, Inc., pp. 725-735.

Examiner
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